

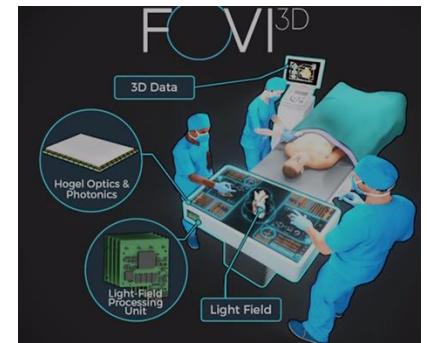
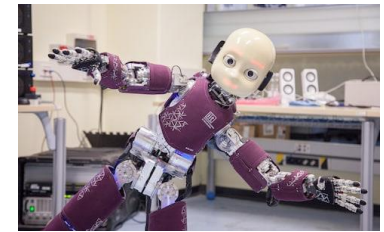
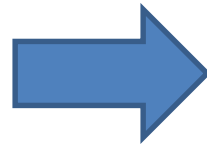
# **More than Moore with Electronic-Photonic Integration**

Vladimir Stojanović

Berkeley Wireless Research Center

UC Berkeley

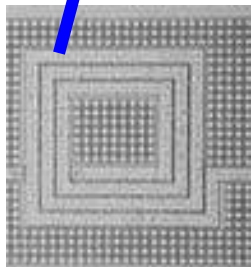
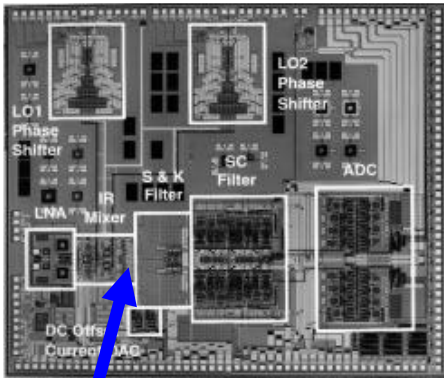
- Milos Popović, Rajeev Ram, Krste Asanović, Michael Watts
- Jason Orcutt, Jeffrey Shainline, Christopher Batten, Ajay Joshi, Anatoly Khilo, Amir Atabaki, Fabio Pavanello, Luca Alloatti, Hanqing Li
- Mark Wade, Karan Mehta, Jie Sun, Josh Wang
- Chen Sun, Sen Lin, Sajjad Moazeni, Nandish Mehta, Michael Georgas, Benjamin Moss, Jonathan Leu, Christos Adamopoulos, Panagiotis Zarkos, Pavan Bhargava, Taehwan Kim
- Yong-Jin Kwon, Scott Beamer, Yunsup Lee, Andrew Waterman, Miquel Planas, Rimas Avizienis, Henry Cook, Huy Vo
- Roy Meade, Gurtej Sandhu and Micron Fab12 team (Zvi, Ofer, Daniel, Efi, Elad, ...)
- Douglas Coolbaugh, Christopher Baiocco and the CNSE fab team
- DARPA, Micron, NSF, BWRC
- IBM Trusted Foundry, Global Foundries



## Enhanced CMOS enables new applications

1997

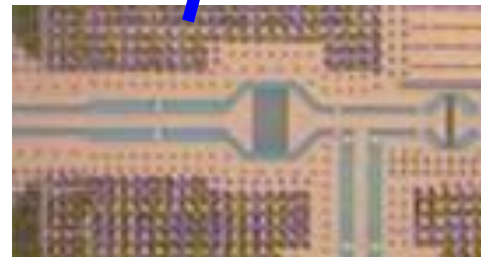
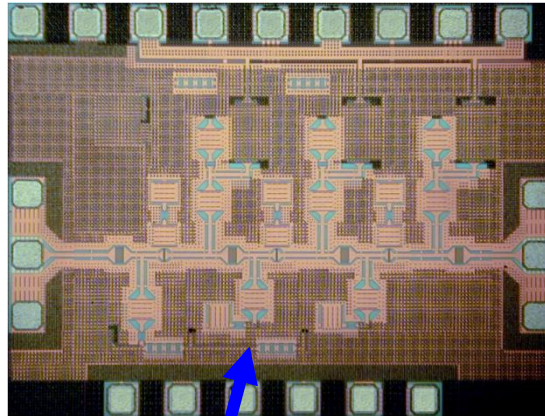
One of the first CMOS radios  
Rudell & Gray



Inductors in IC process  
Nguyen & Meyer  
1990

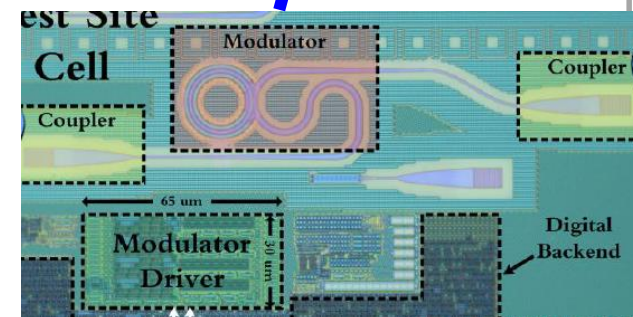
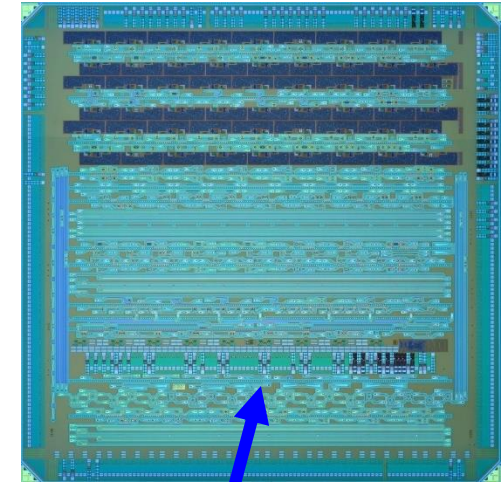
2004

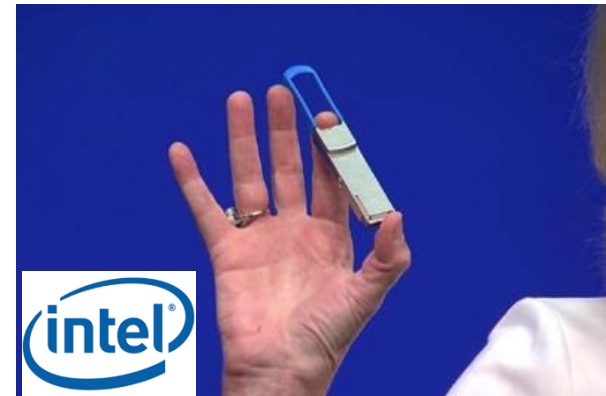
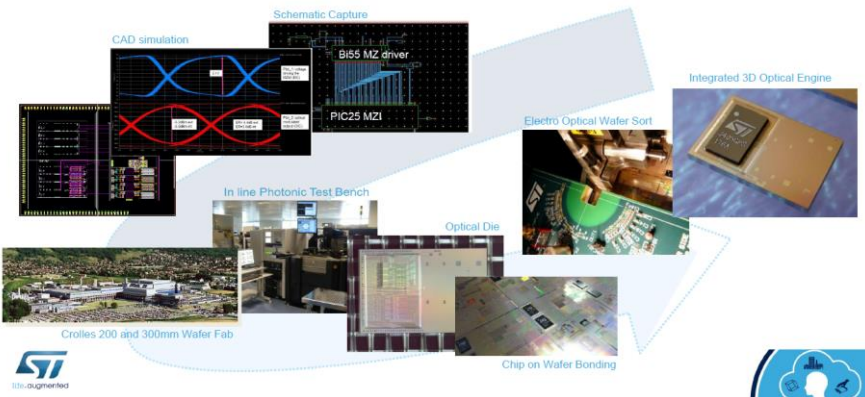
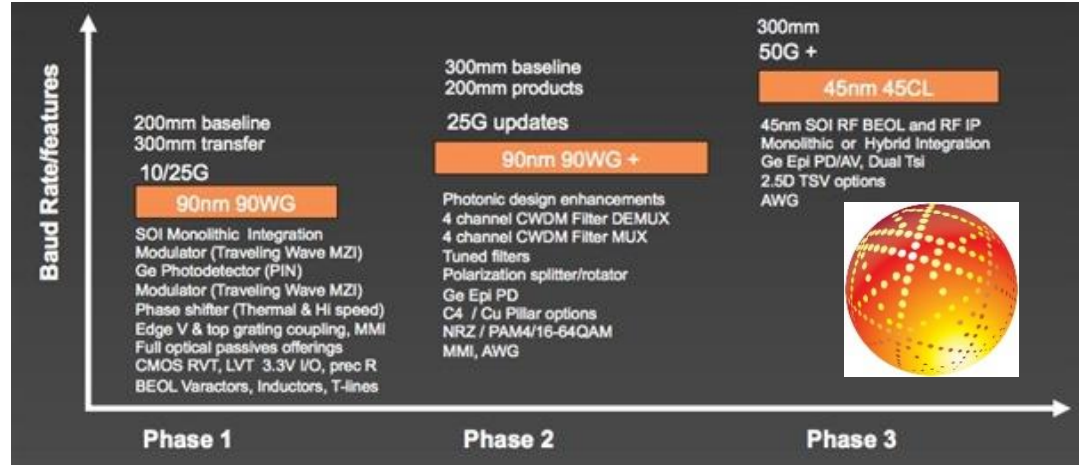
World's first 60GHz CMOS Amplifier  
Niknejad & Brodersen



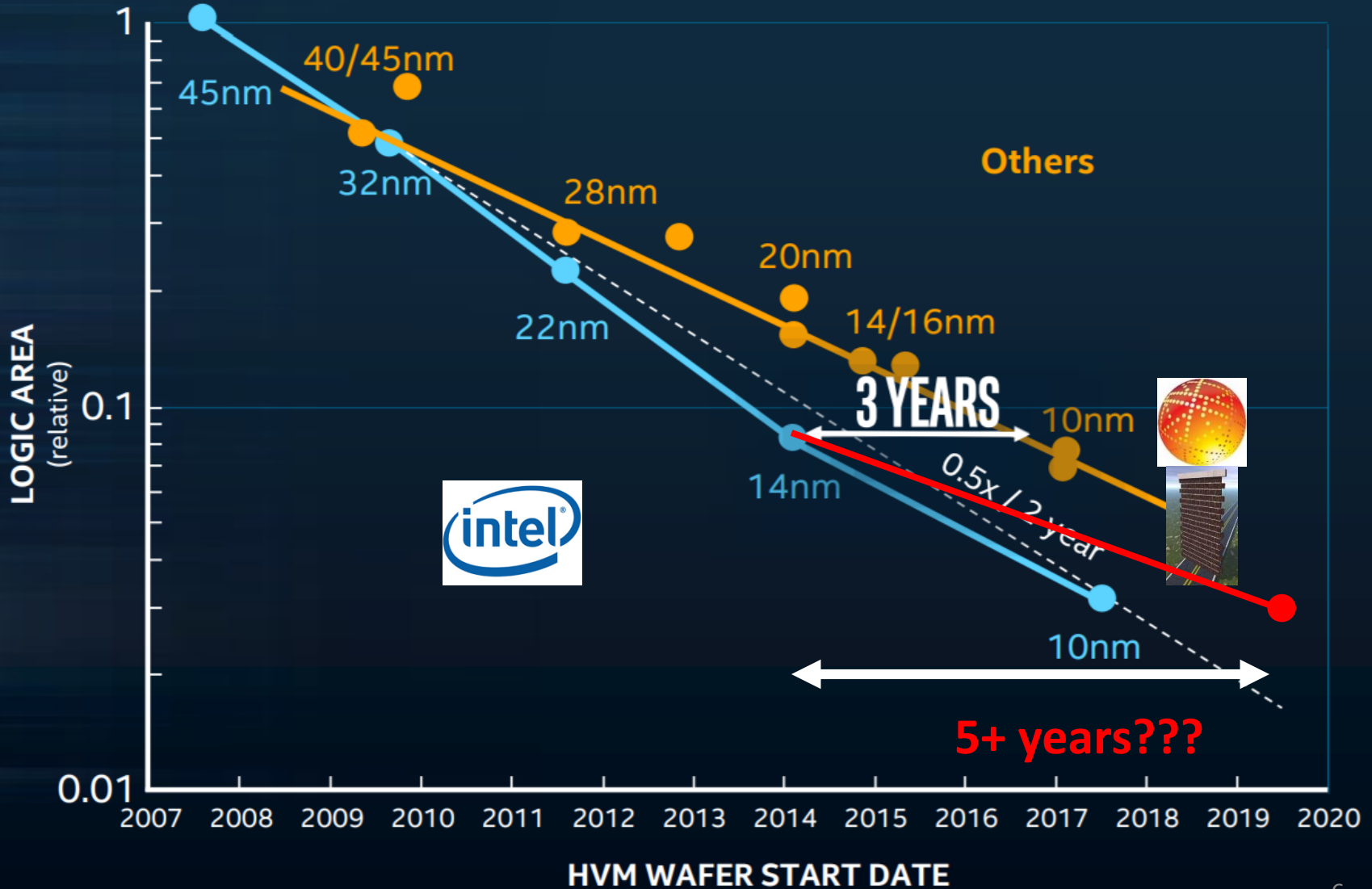
2012

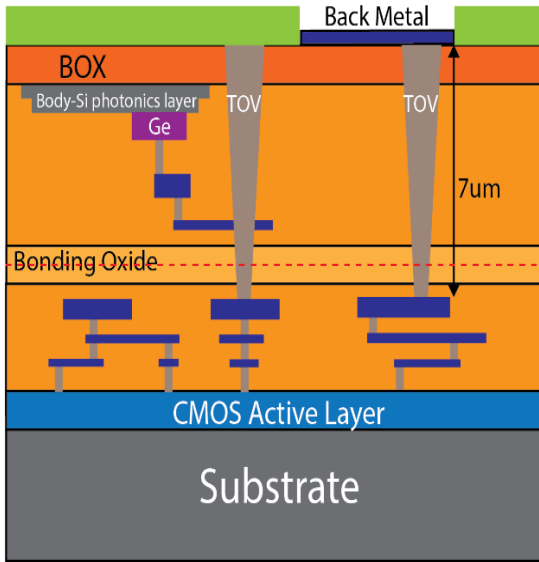
World's first siPhotonic transmitter in 45nm SOI  
Stojanovic, Popovic, Ram





- Every major foundry has a Silicon-Photonic process



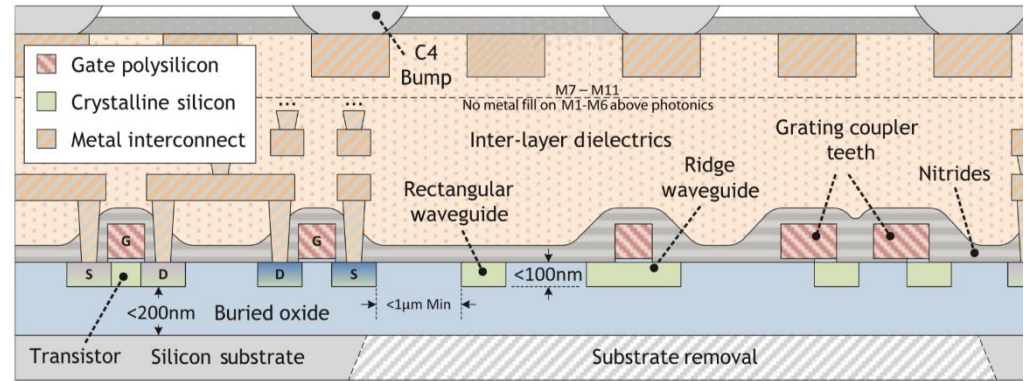


Flipped  
Photonic  
Wafer

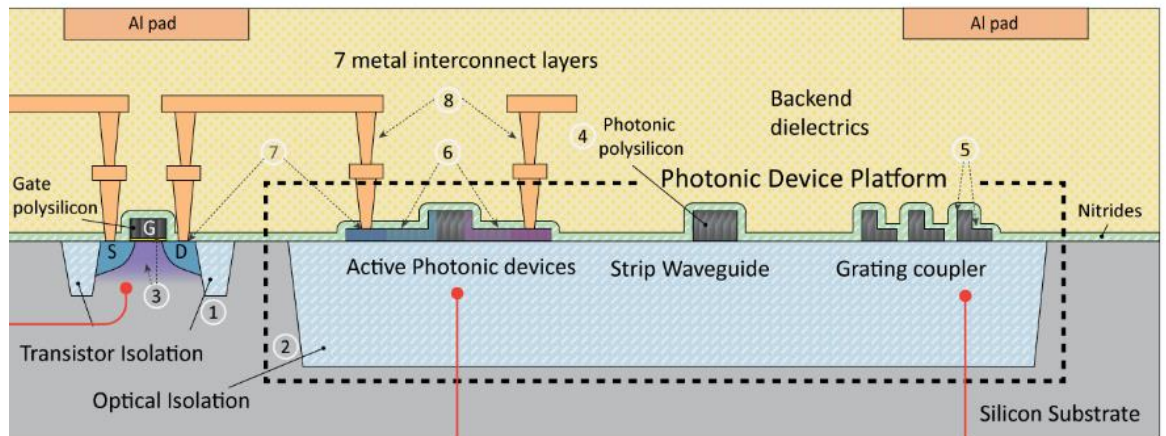
CMOS  
Wafer

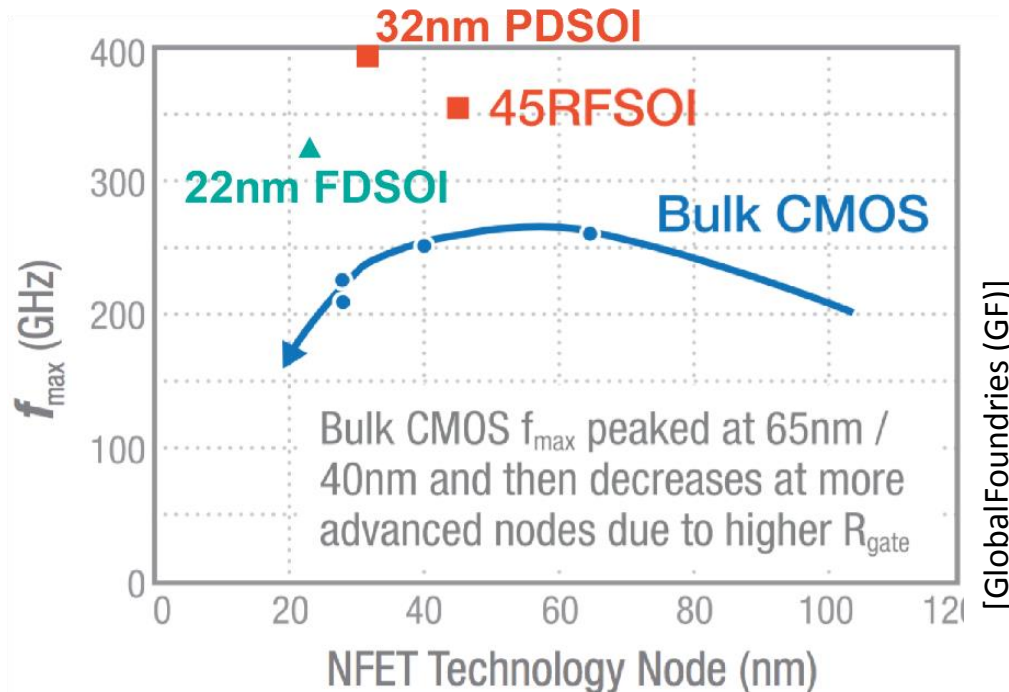
Fully-Customized SOI  
Photonics (CNSE)  
+ any CMOS (currently  
65nm bulk)

“Zero-change” (45nm and 32nm SOI)



Deposited Photonics  
180nm (Micron) and 65nm (CNSE) **bulk CMOS**

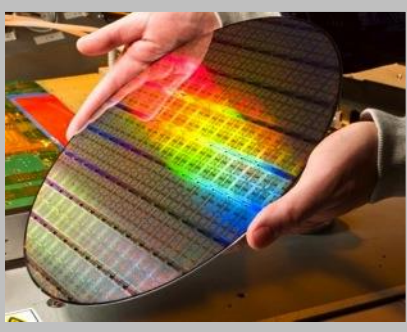




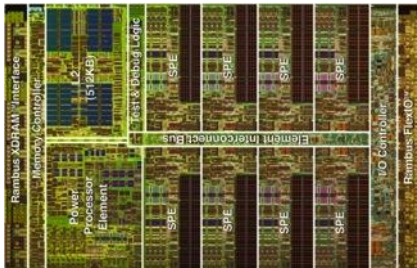
- $f_T/f_{max}$  have not improved since 32nm node
- $f_T/f_{max}$  affect speed, energy-efficiency, ... of electronic-photonic systems
- **32/45nm: Fastest Transistors + Thick-enough Si bodies to guide the light**
  - Si body in SOI nodes below 32nm (FDSOI) cannot guide the light!



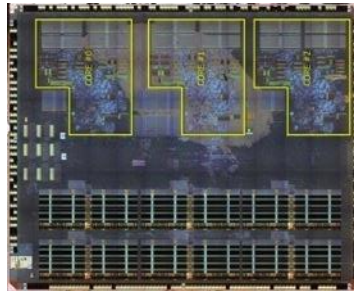
- 300mm wafer, commercial process
- MOSIS and TAPO MPW access
- Advanced process used in microprocessors
- Photonic enhancement enables VLSI photonic systems (no required process changes)



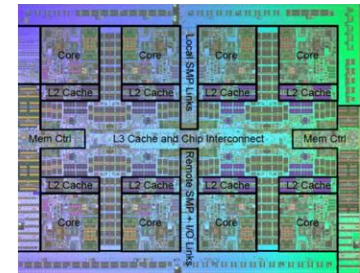
## IBM Cell

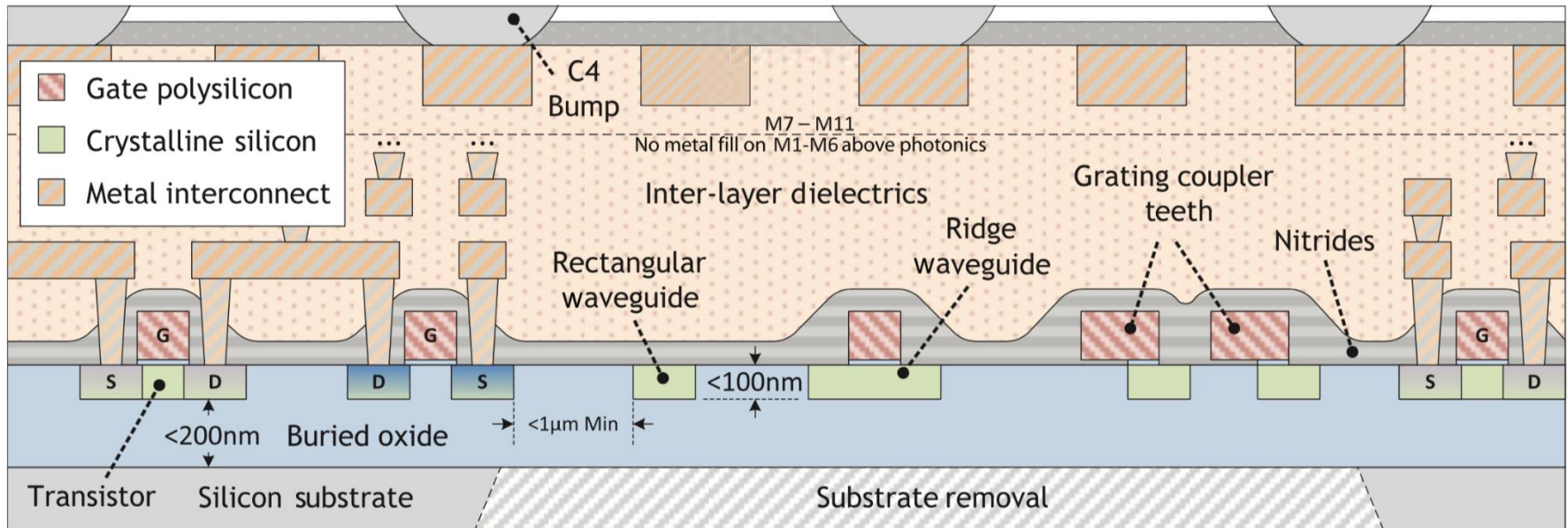


## IBM Espresso



## IBM Power 7





[C. Sun, JSSC 2016]

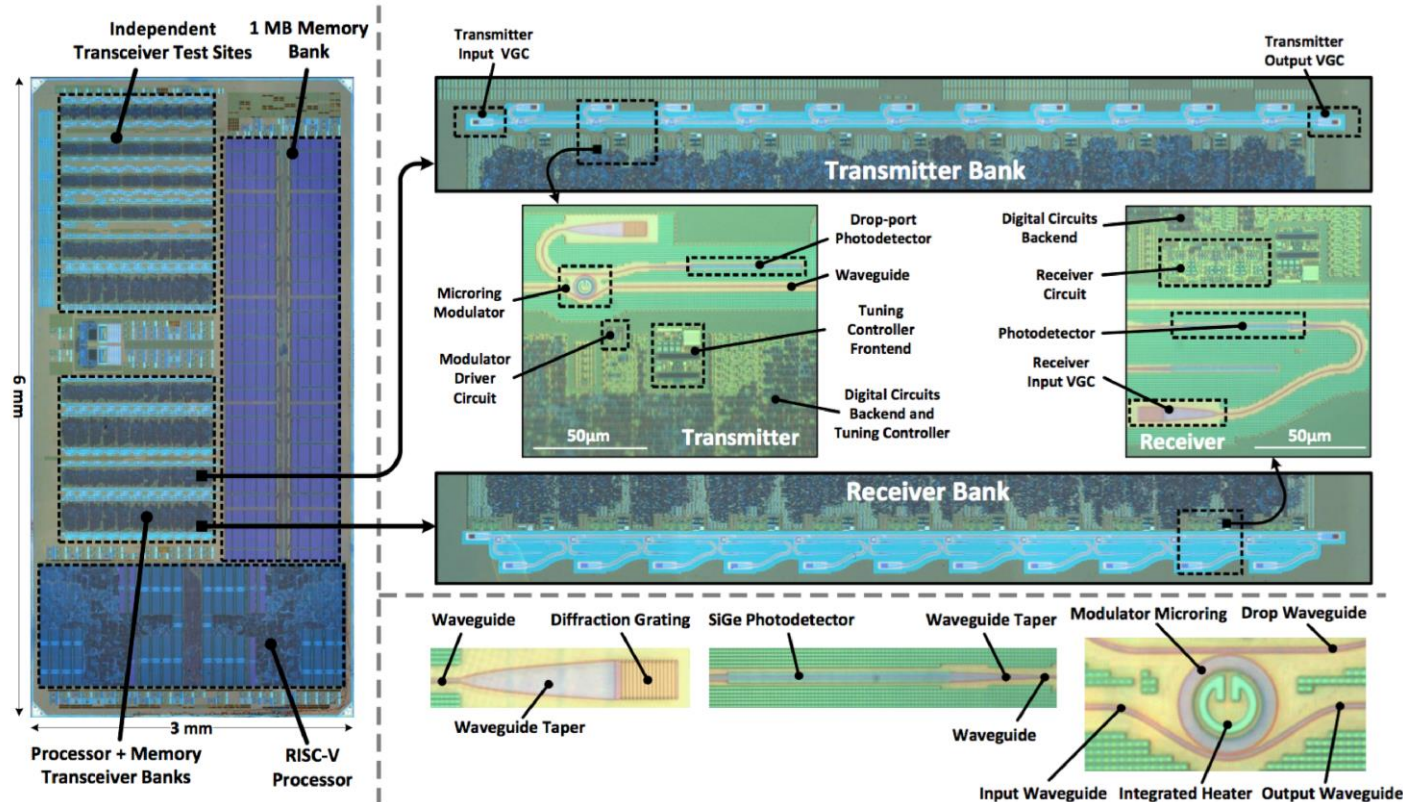
- Photonics for free! (No modification to the process)
- Closest proximity of electronics and photonics
- Single substrate removal post-processing step

**Monolithic photonics platform with the fastest transistors**

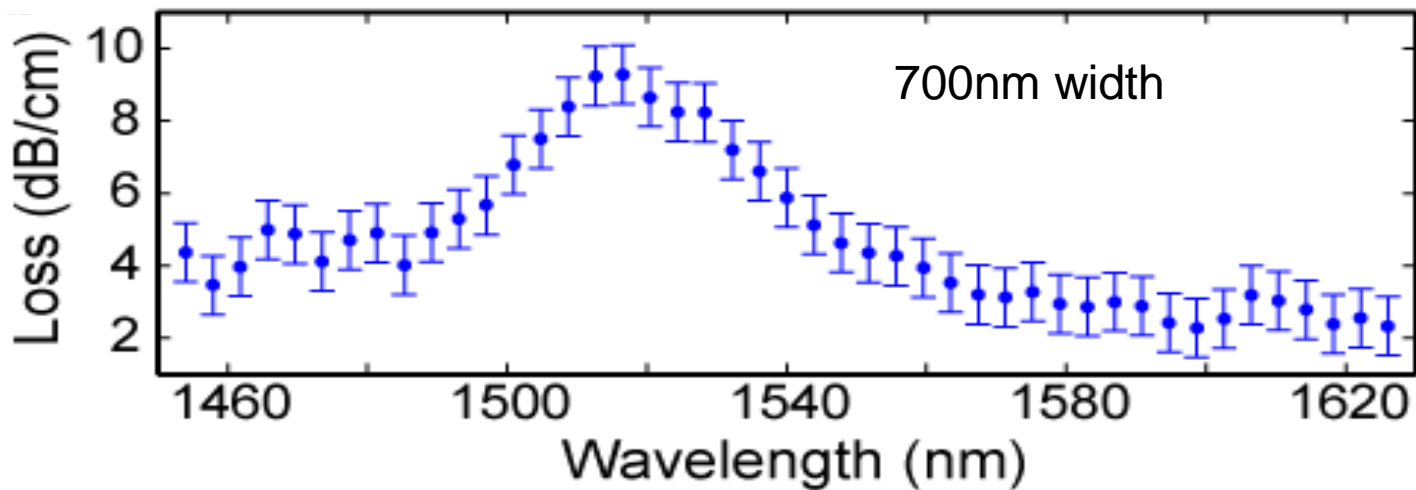
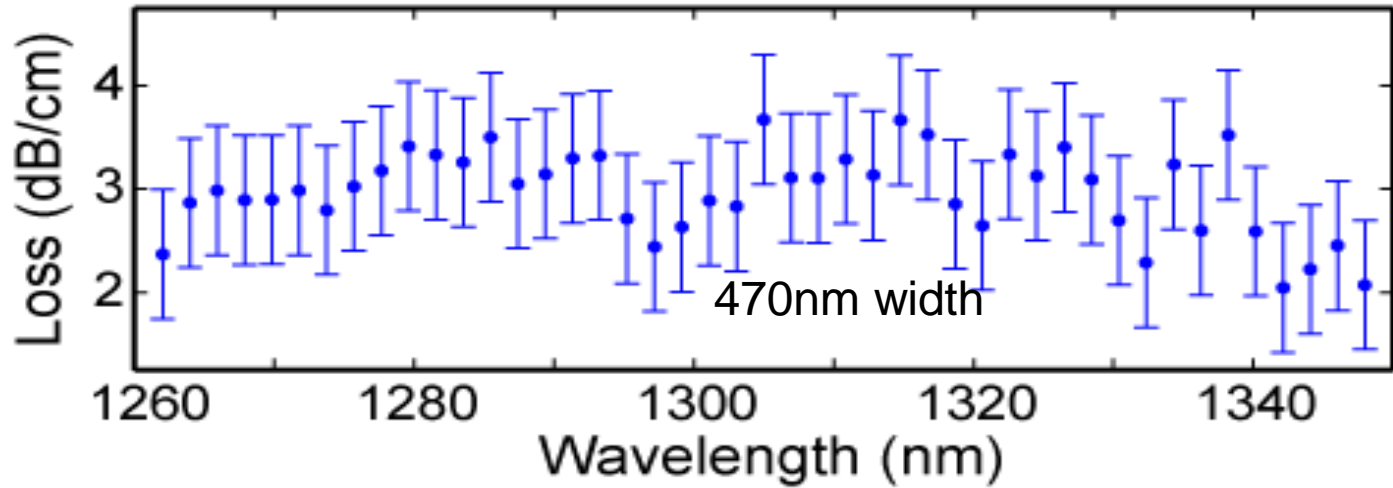
## Silicon-Photonic components integrated directly in the chip

Zero-change  
45nm SOI

DARPA POEM & PERFECT – Stojanović, Ram, Popović, Asanović  
70+M transistors, thousands of photonic devices



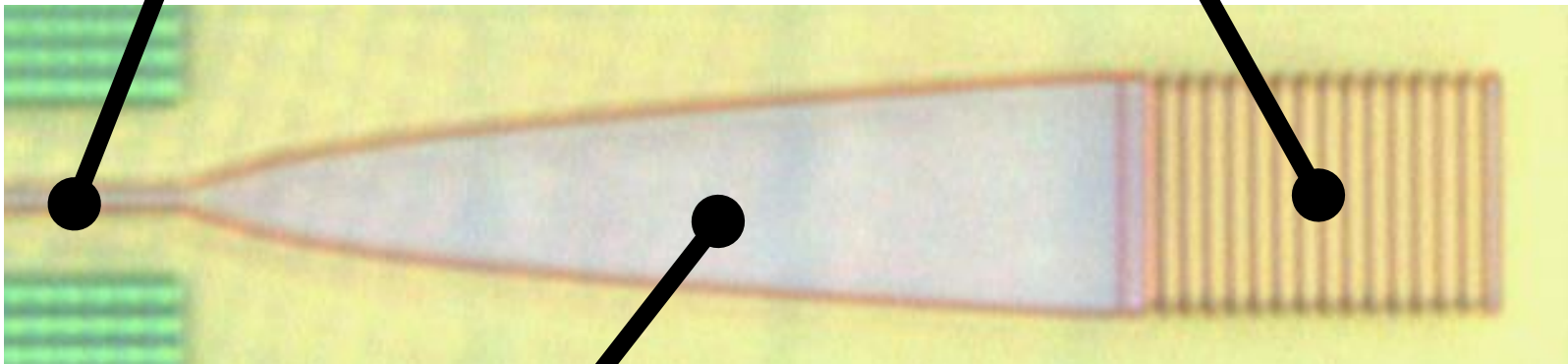
*C. Sun et al. Nature, Dec. 15.*



Vertical couplers

**Waveguide**

**Diffraction Grating**

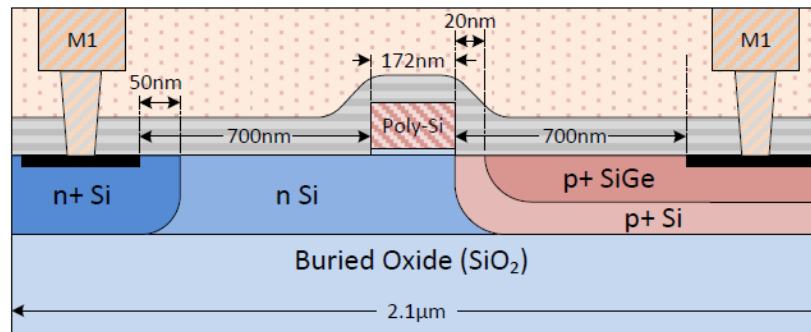
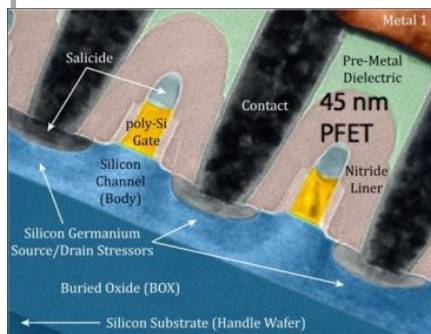
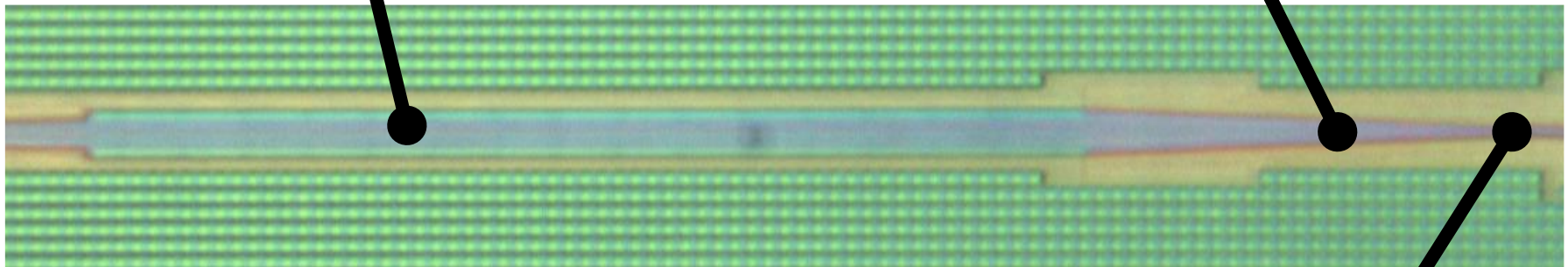


**Waveguide Taper**

SiGe from PMOS strain engineering used in Photodetectors

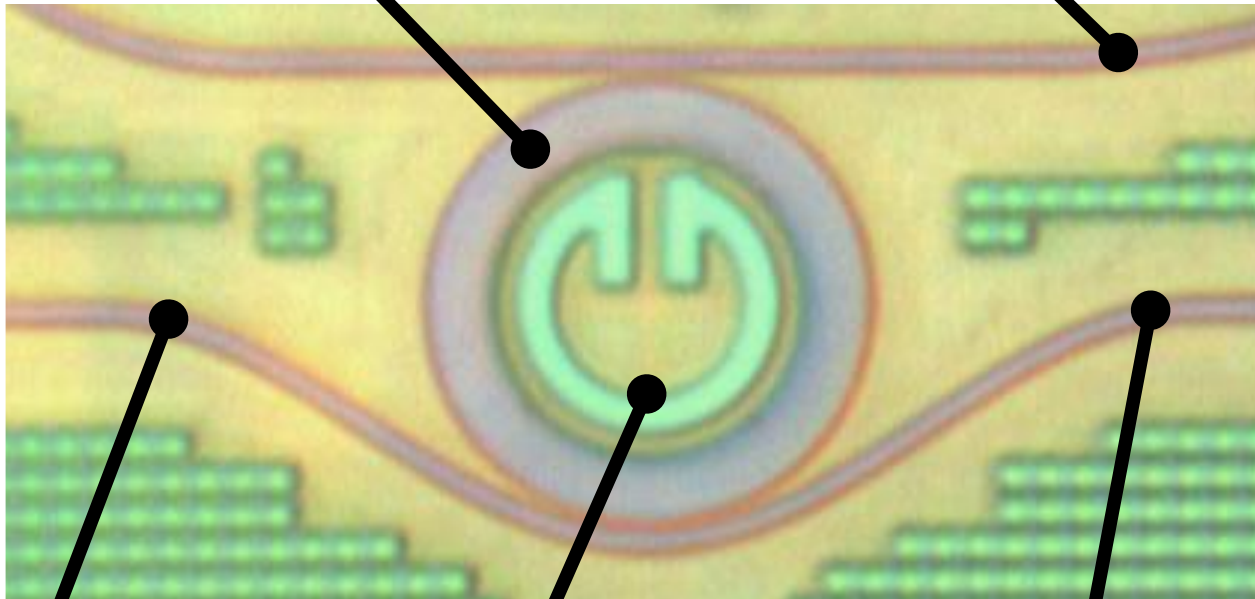
## SiGe Photodetector

## Waveguide Taper



## Waveguide

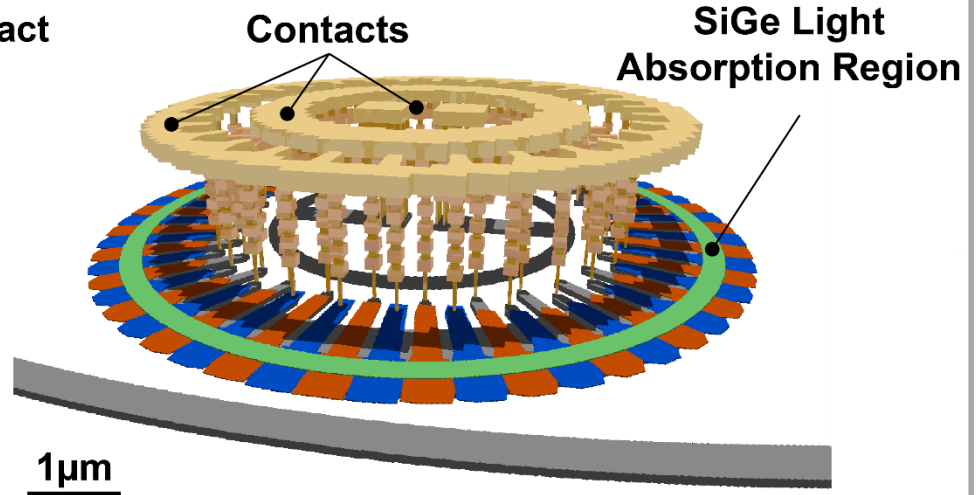
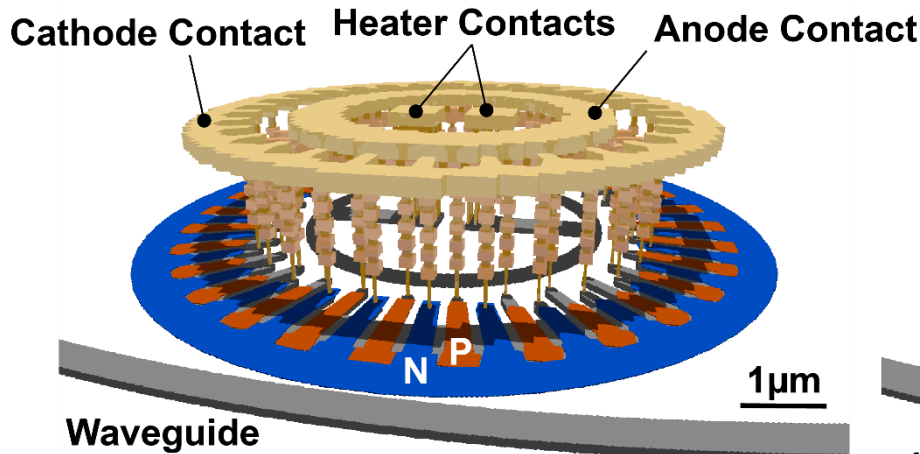
**Modulator Microring Drop Waveguide**



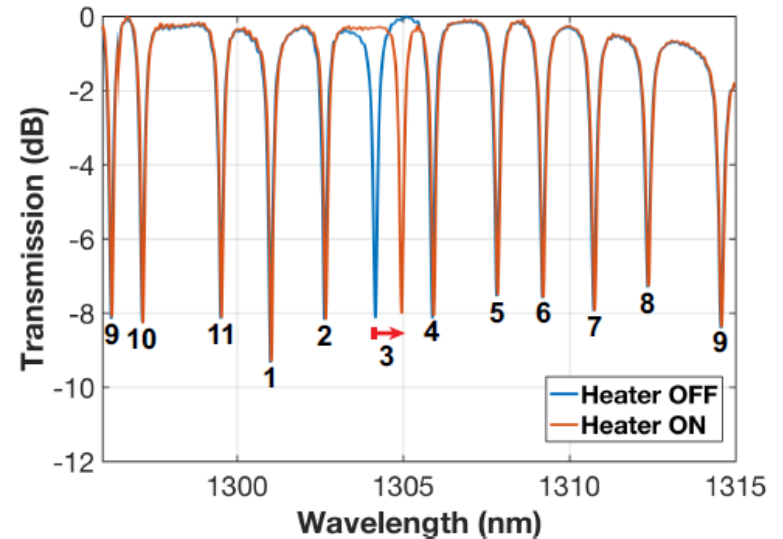
**Integrated Heater Output Waveguide**

**Input Waveguide**

[Shainline OL 2013, Wade OFC 2014]

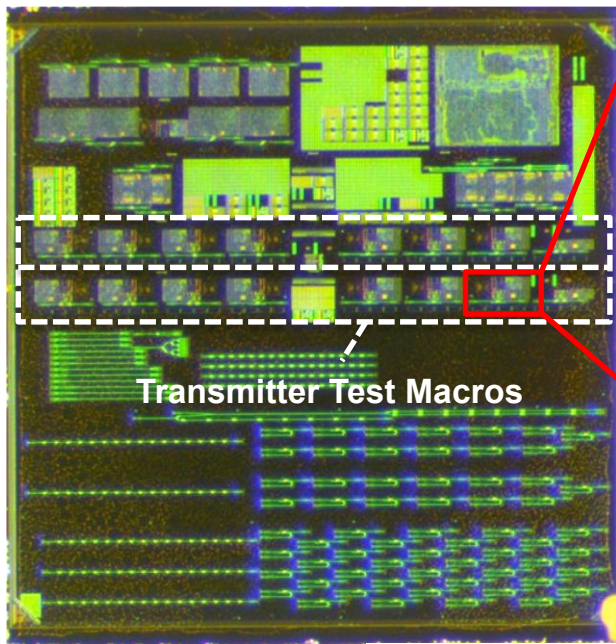


- Interleaved planar PN junctions
  - Enabled by advanced lithography of this process
- Highly sensitive structures that can be used in a number of applications
  - Q factors up to 200k





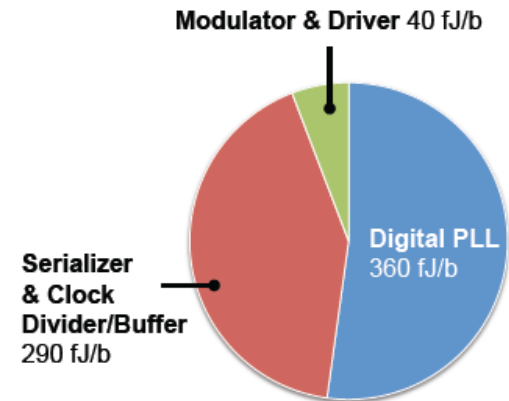
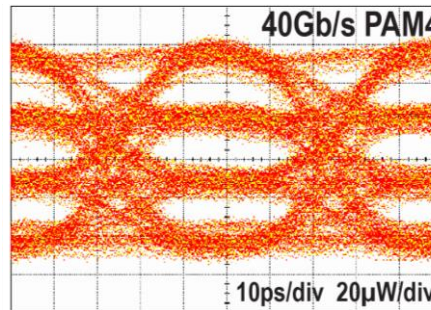
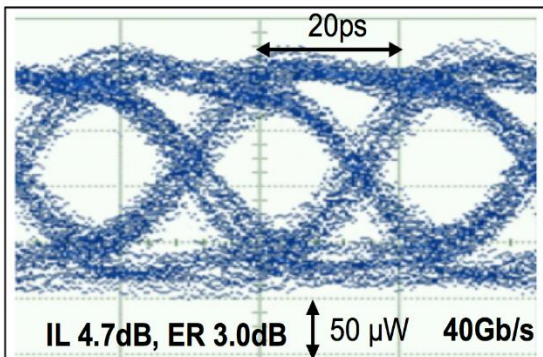
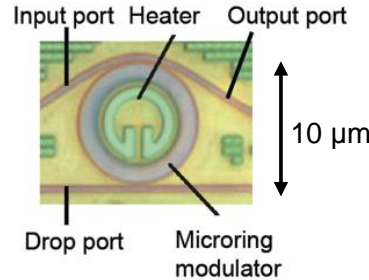
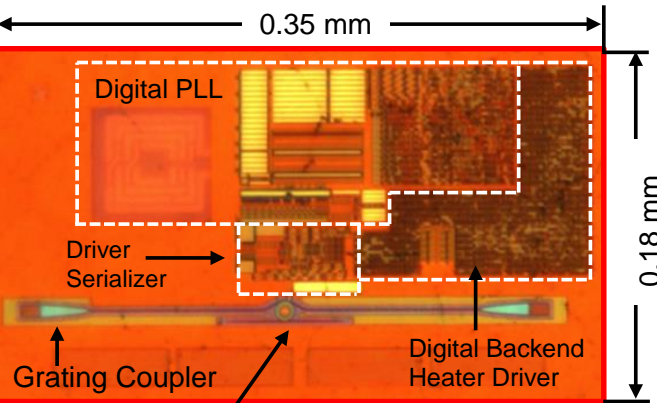
Moazeni and Lin et al [ISSCC17, JSSC17, OptEx18]



Transmitter Test Macros

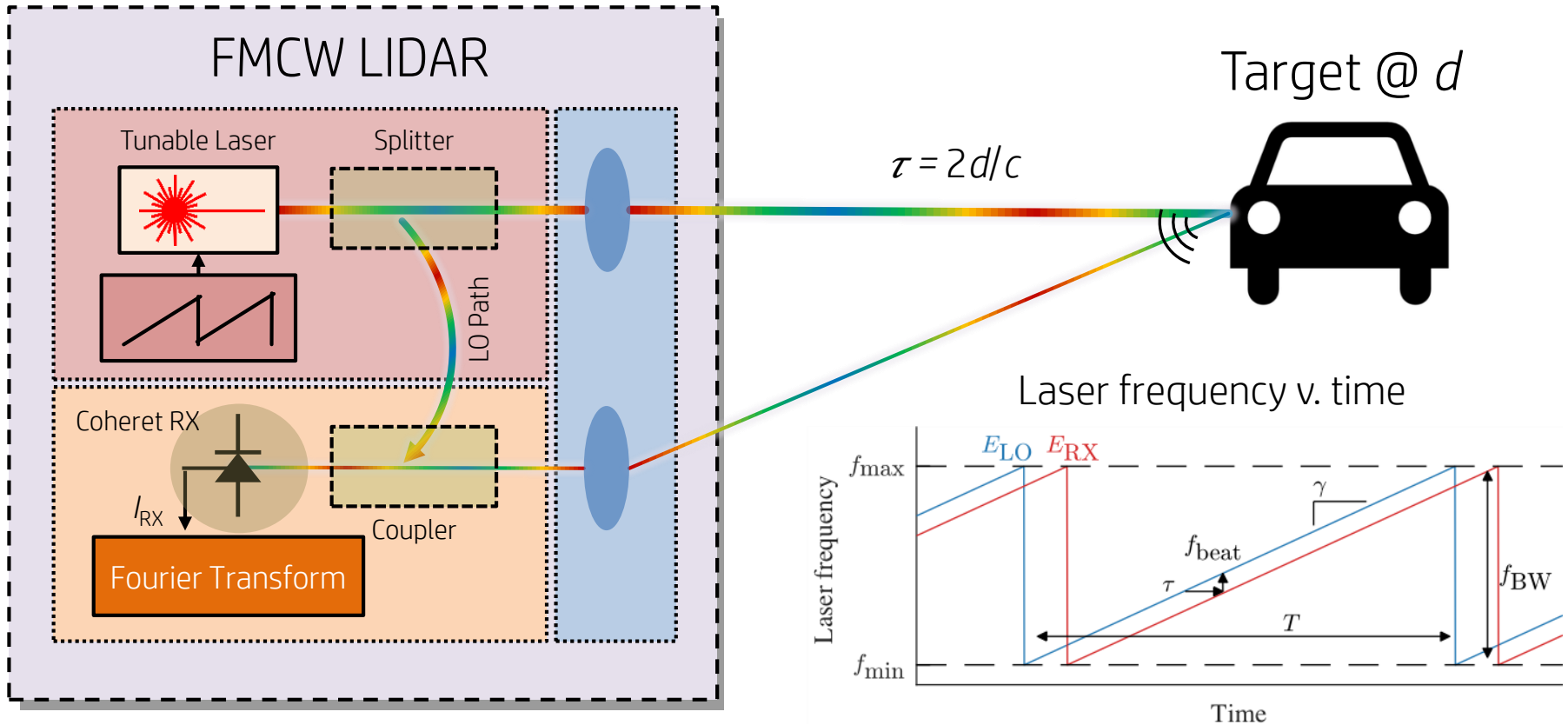
Chip 3.0x3.0mm

Transmitter Macro

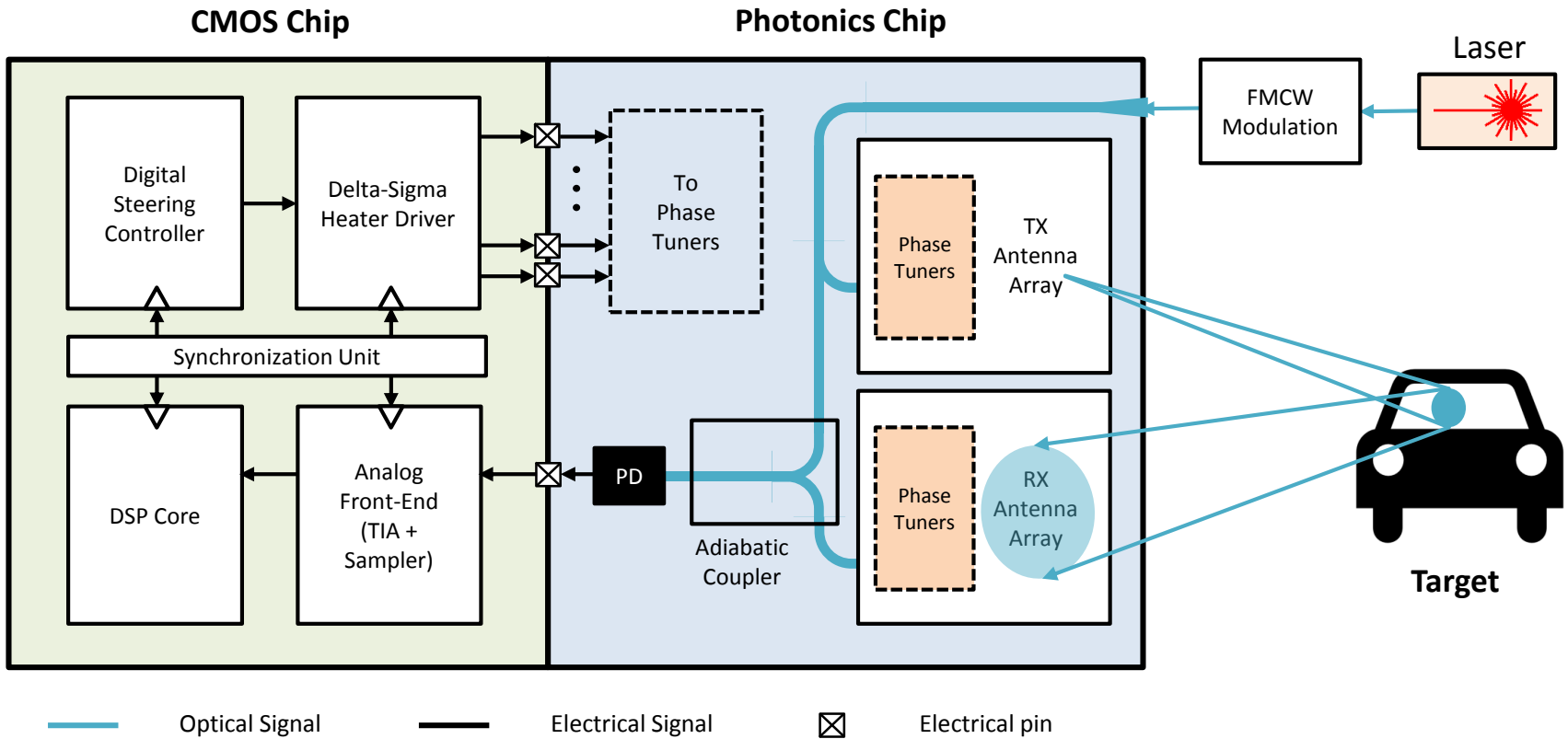


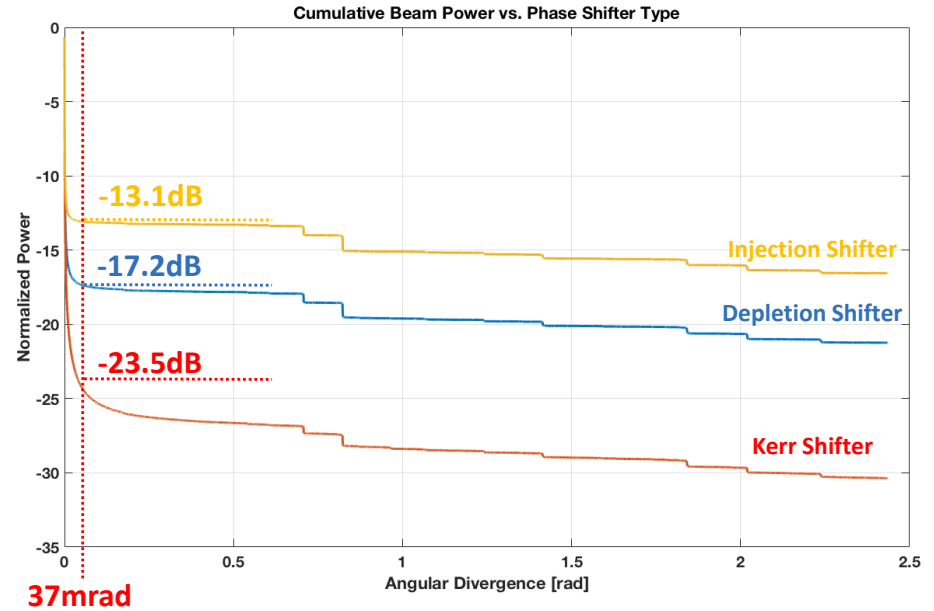
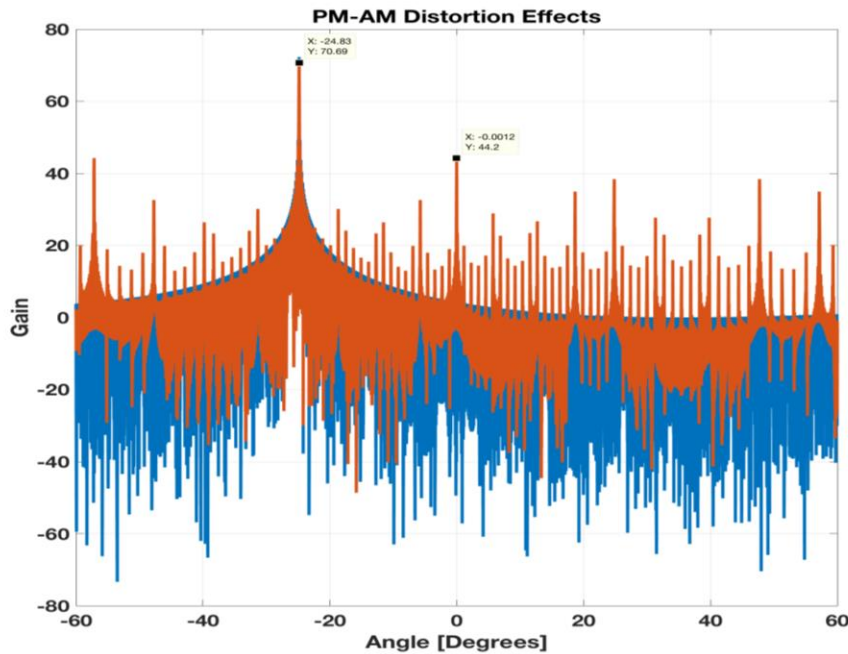
<b>Modulation</b>	40 Gb/s NRZ
<b>Full TX Energy</b>	0.33 pJ/b
<b>Full TX + PLL</b>	0.69 pJ/b

## Anatomy of FMCW LIDAR

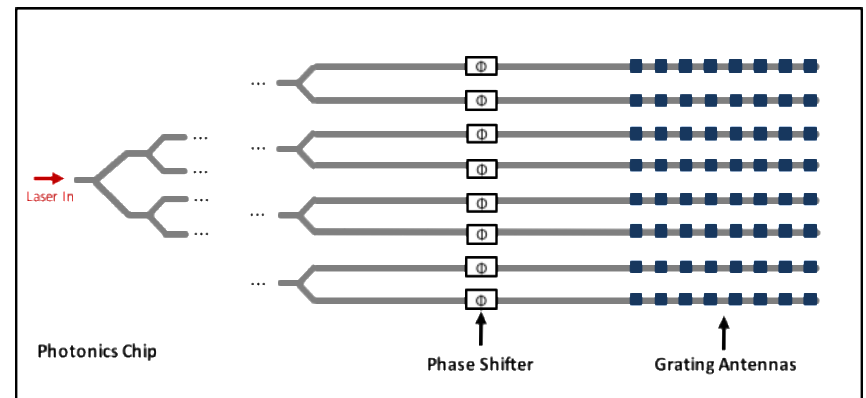


- Advantages over pulsed LIDAR
  - Sensitivity shot-noise limited
  - Less sensitive to background noise

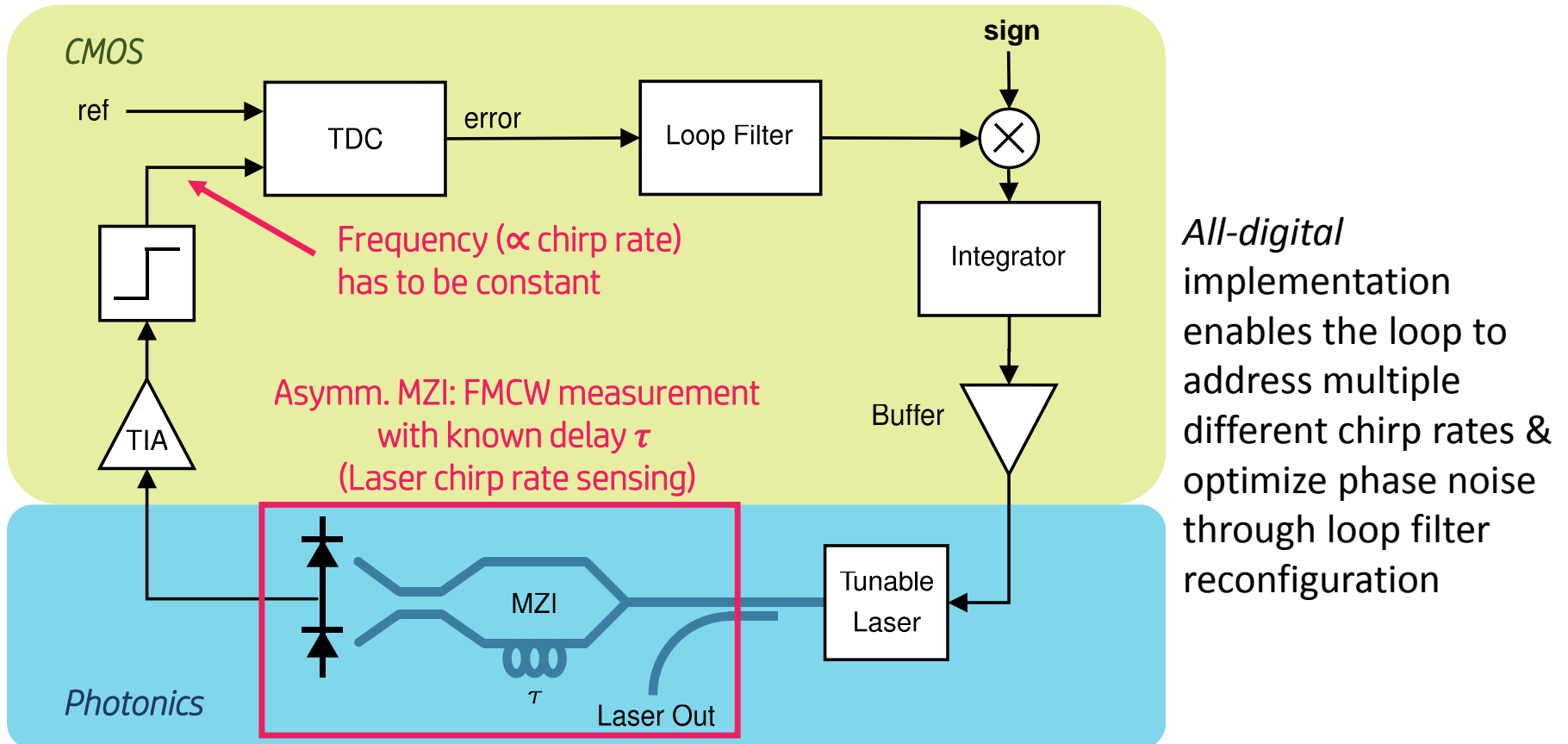




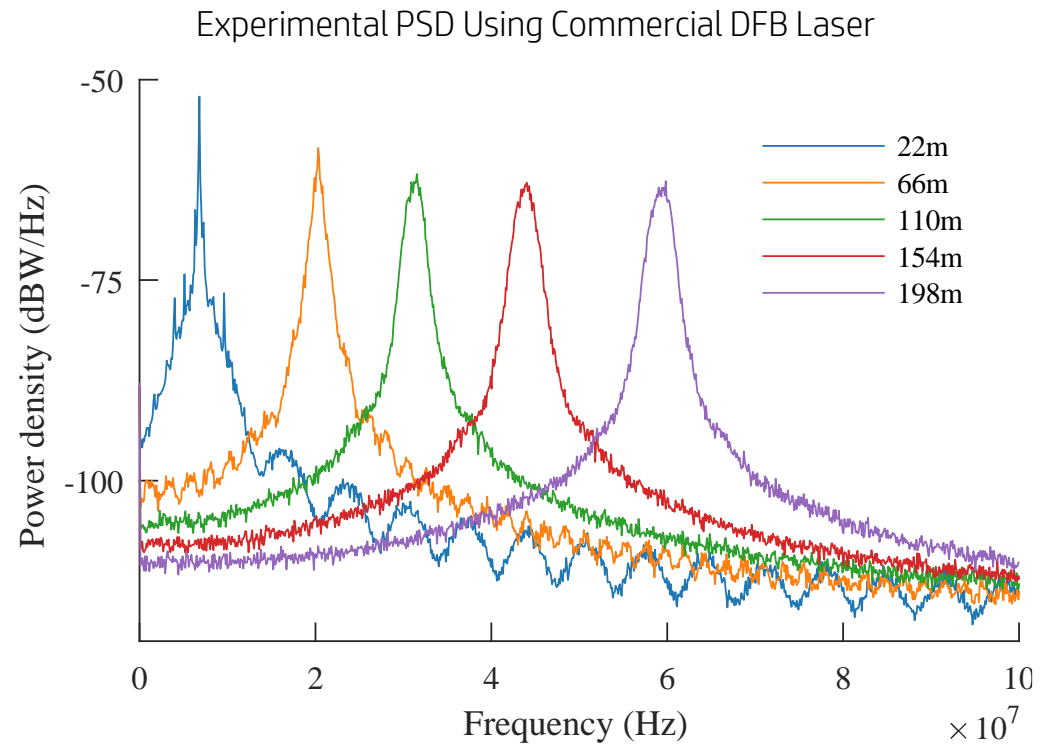
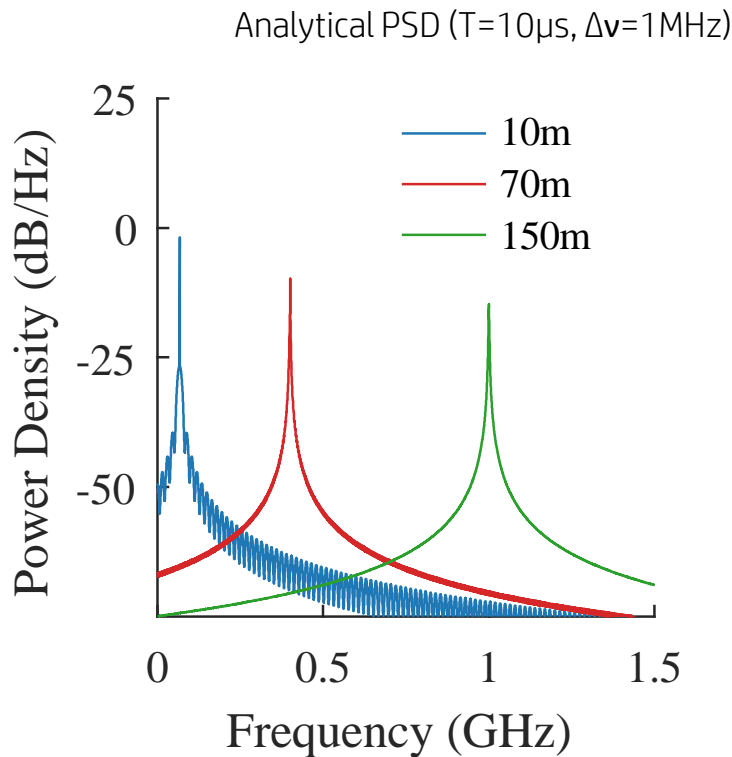
- Extensive modeling framework
  - Various phase-shifter types (AM/PM distortion)
  - Quantization
  - Index variations, coupling and pitch mismatch, etc



- Optical PLL enables closed-loop control of laser wavelength

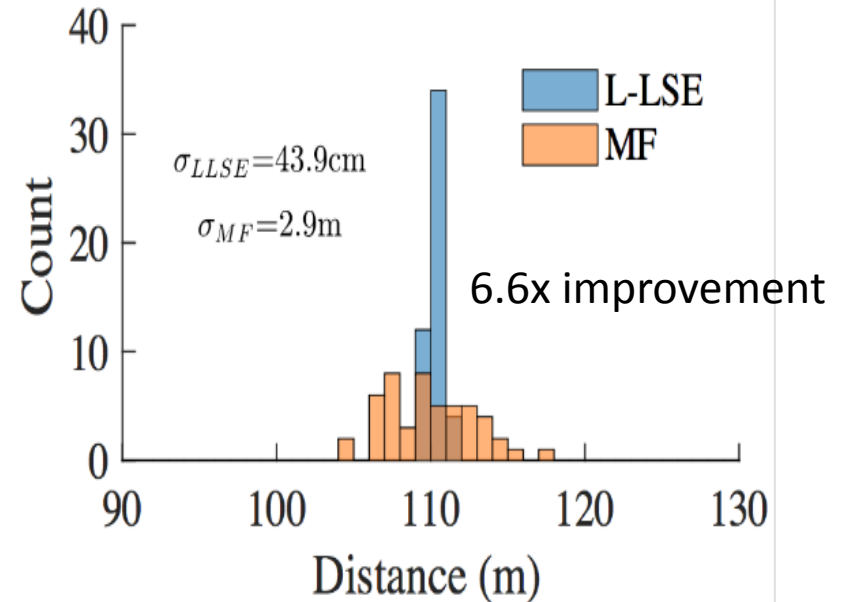
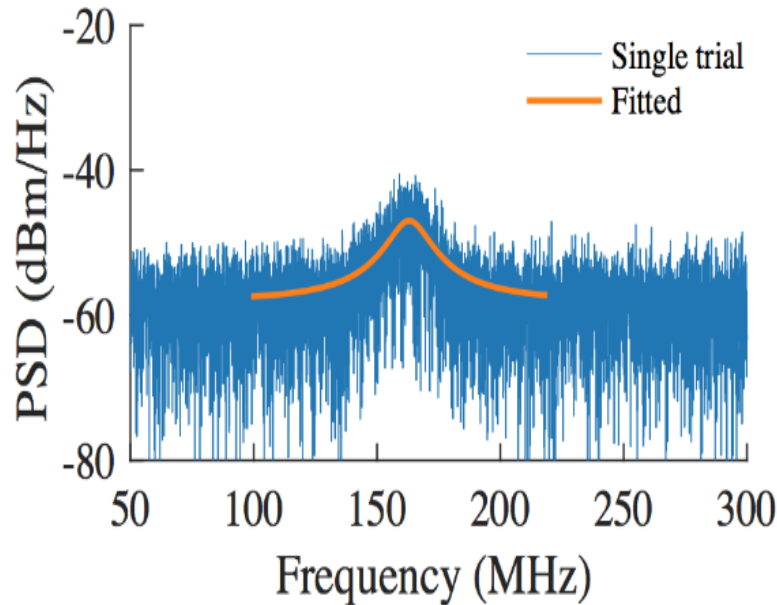


- Chips currently in packaging
  - CMOS: GF 45nm SOI process
  - Photonics: CNSE 300mm process



- Spectral peak degrades as distance increases ( $\propto e^{-\Delta\omega\tau}$ )
  - Beyond “coherence distance,” lineshape converges to laser lineshape (e.g. Lorentzian)
  - Big challenge for using compact semiconductor lasers (>1MHz linewidth) for long-distance (>100m) LIDAR

[Kim et al ICASSP18, CLEO18]



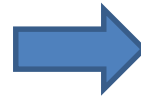
- Improved detection algorithm

- Take into account the phase-noise basis shape

- Wide-range tunable laser with DBR mirror used ( $\Delta\nu \sim 1\text{MHz}$ )
- Path delay (110m) emulated by long fiber, path loss emulated by VOA
- Simulated path loss  $\sim -80\text{dB}$  (corresponding to 110m target, 3x3mm aperture)

## Future MIMO System Challenges

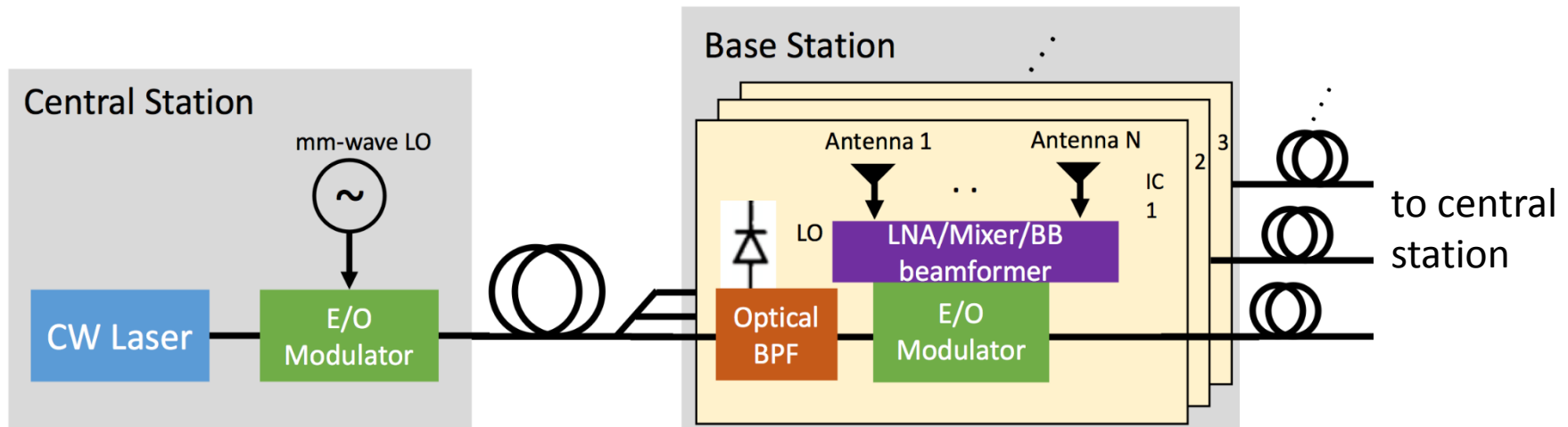
- mm-wave operating frequency
- 100's of beams, 1000's of antennas
- Power
- Density
- Chip-to-chip communication



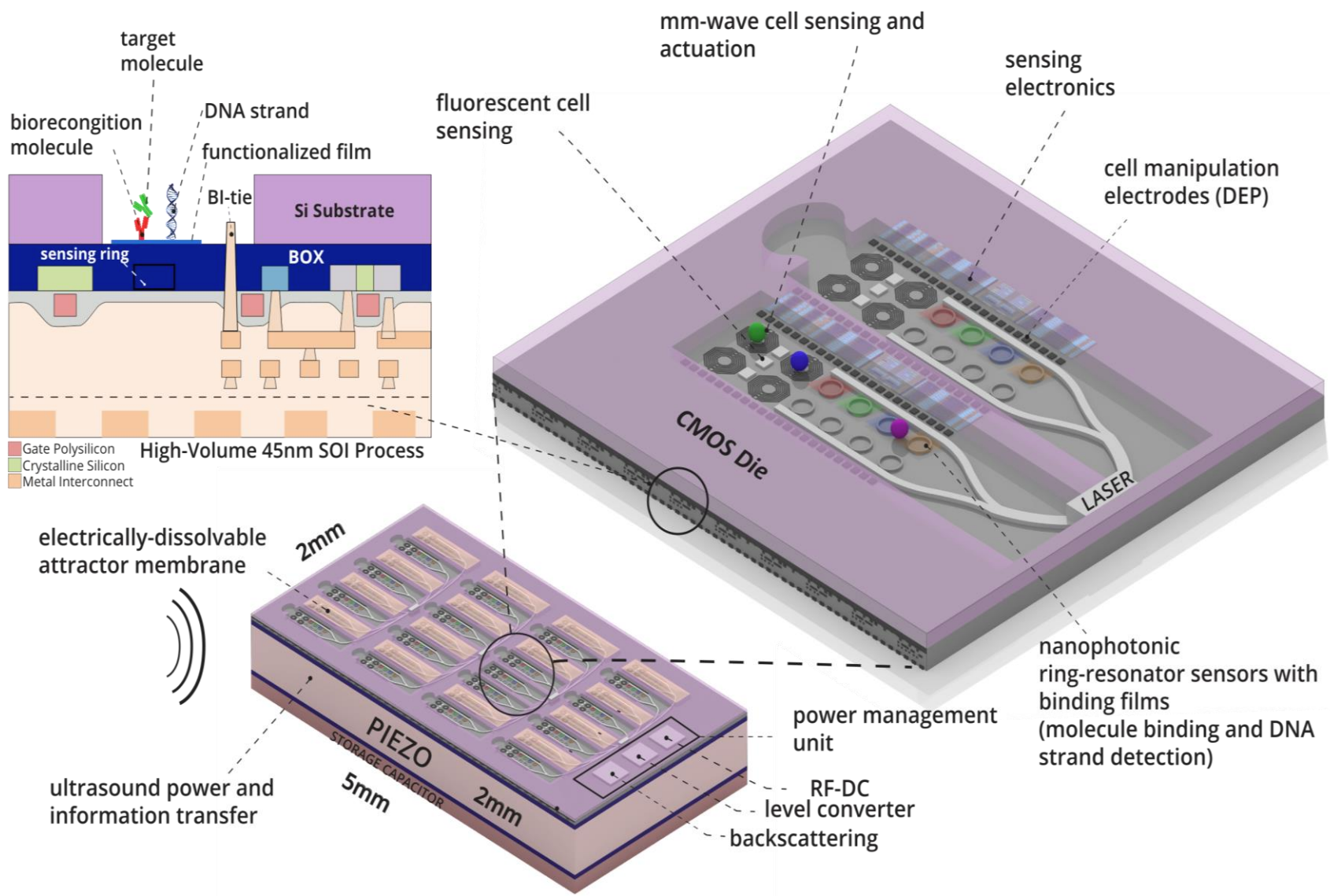
## Electronic-Photonic System Goals

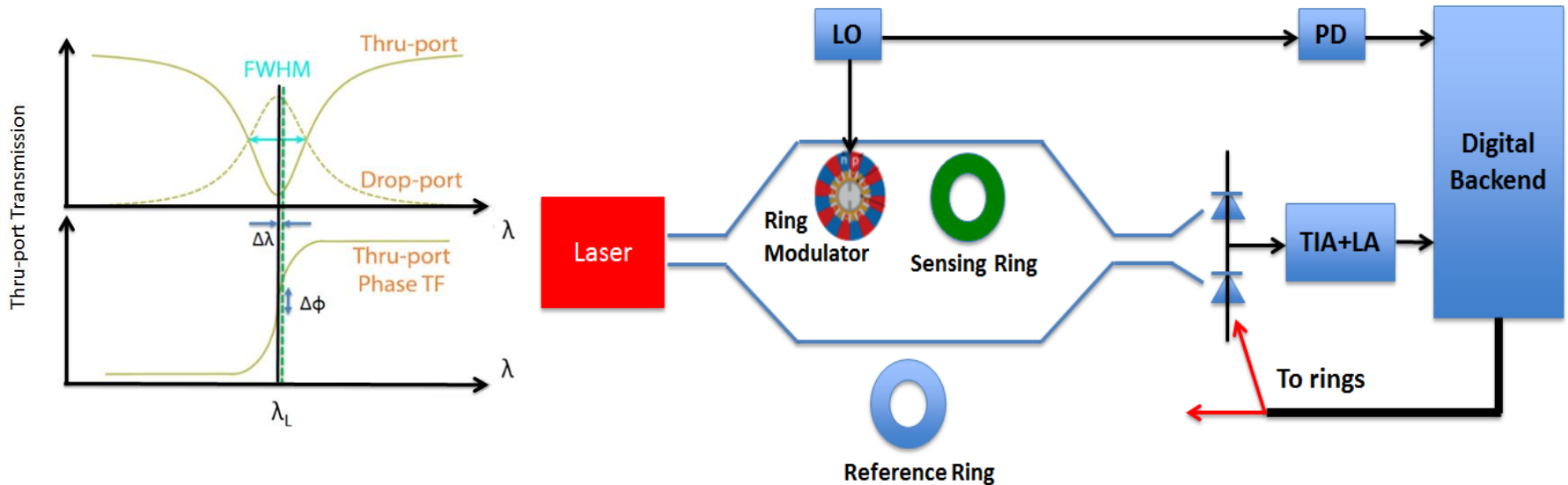
- mm-wave LO distribution
- Direct mm-wave photonic link from antenna to remote hub

NF and SNDR relaxed in massive MIMO systems



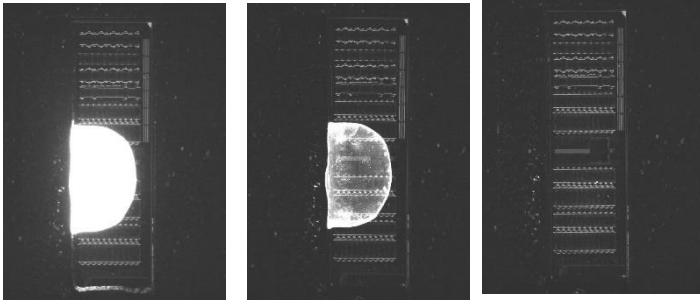






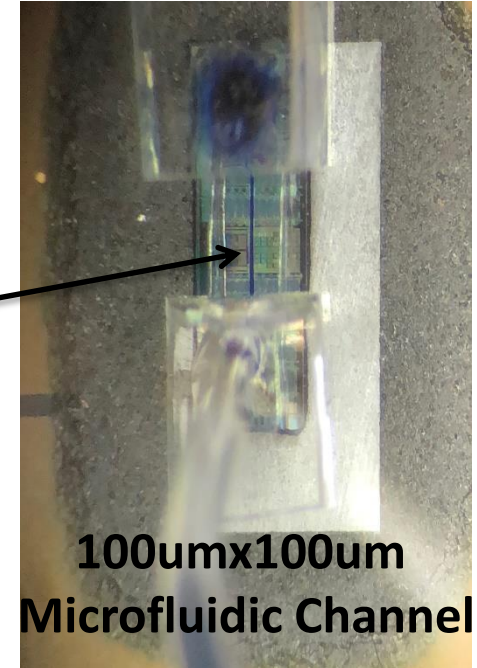
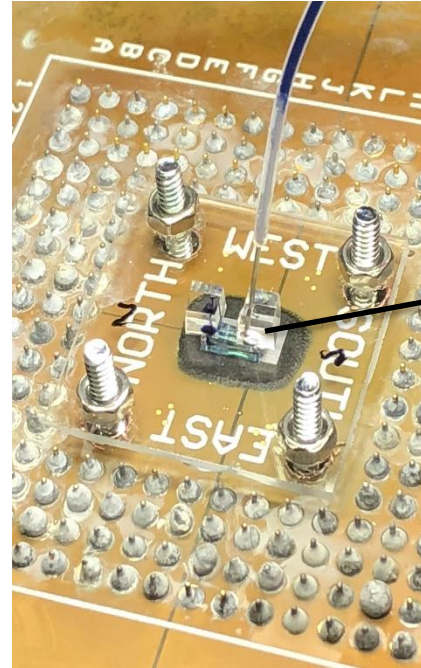
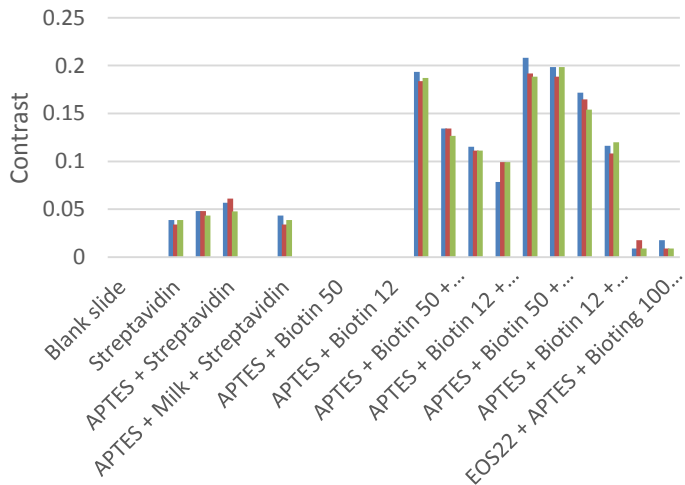
- Reduced measurement time (sub 1s)
  - Capture faster kinetics
- Increased SNR (allows lower ring Q factors)
- Integrated thermal tracking

Wet Streptavidin - fluorophore	Dry Streptavidin - fluorophore	Post Wash
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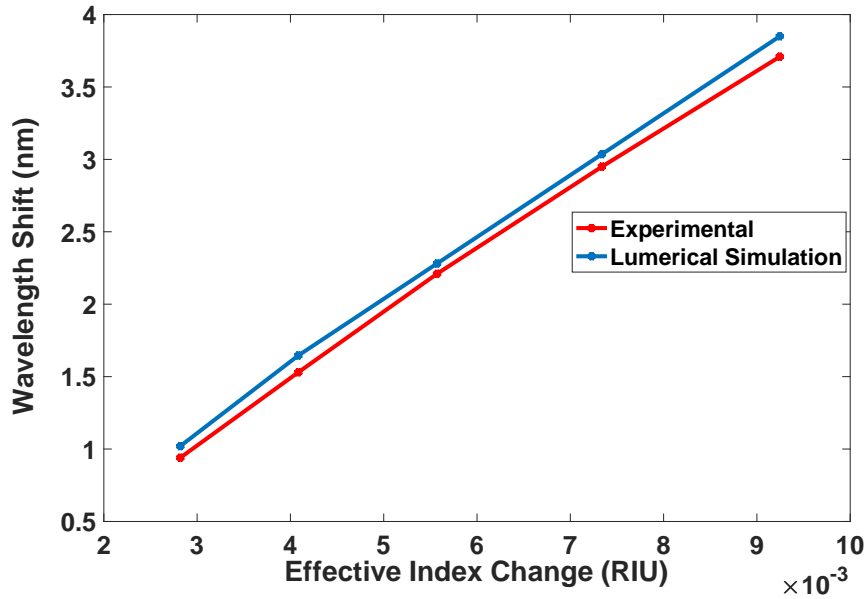


APTES Chip

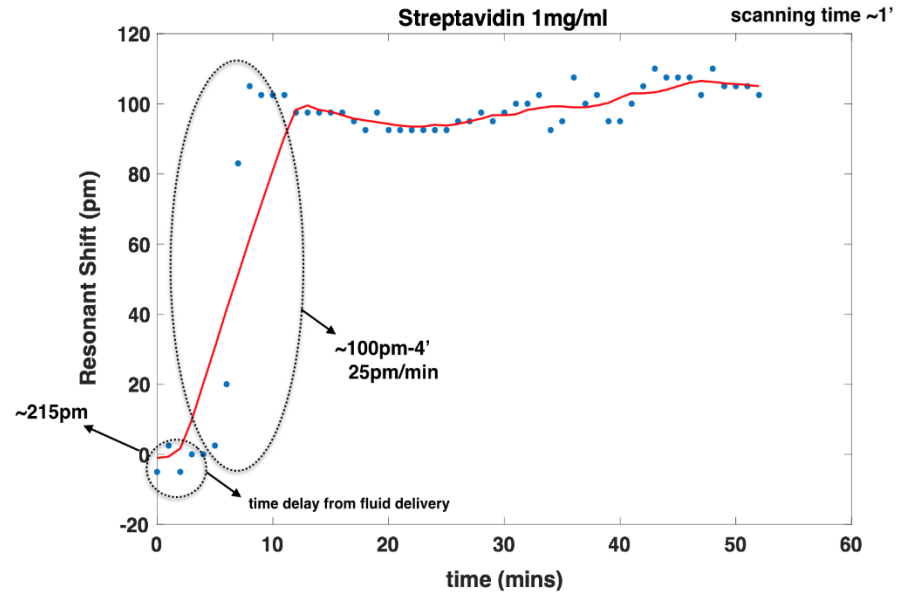
Fluorescence at various conditions



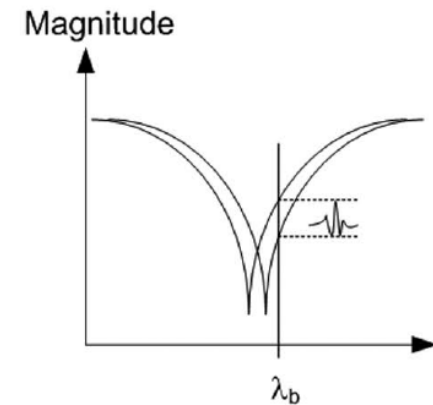
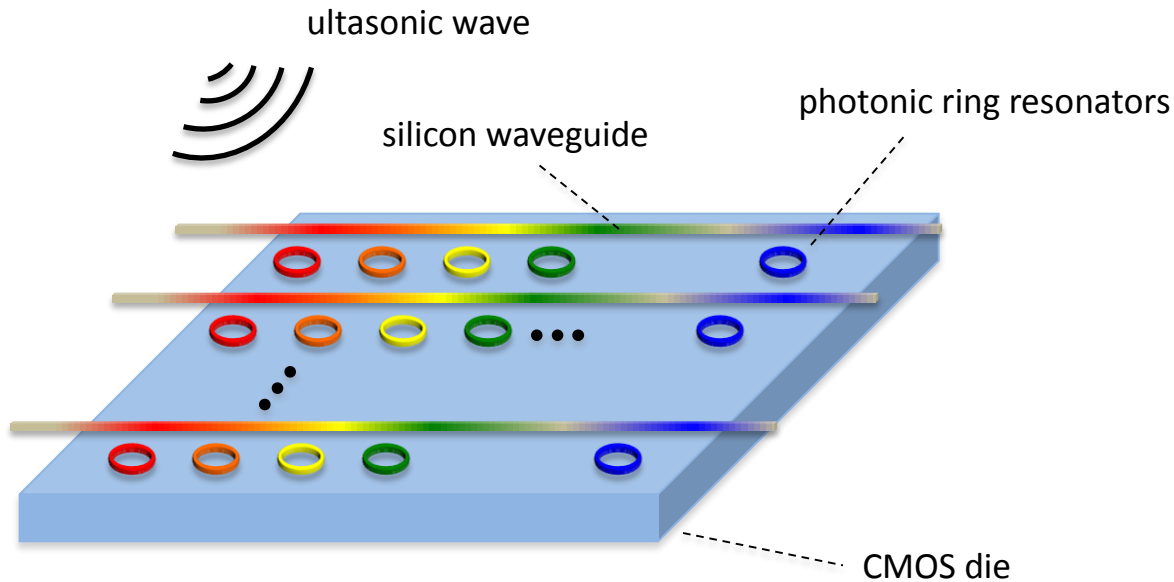
- Substrate released chip (45nm SOI)
  - Successful functionalization with APTES/biotin and biotin-streptavidin binding



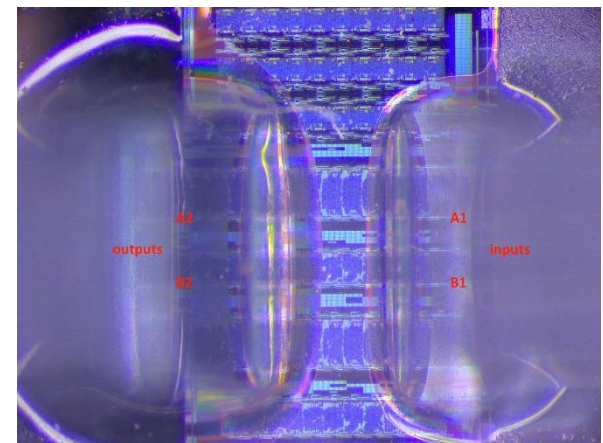
**Bulk RI Sensitivity : 5nm/RIU**

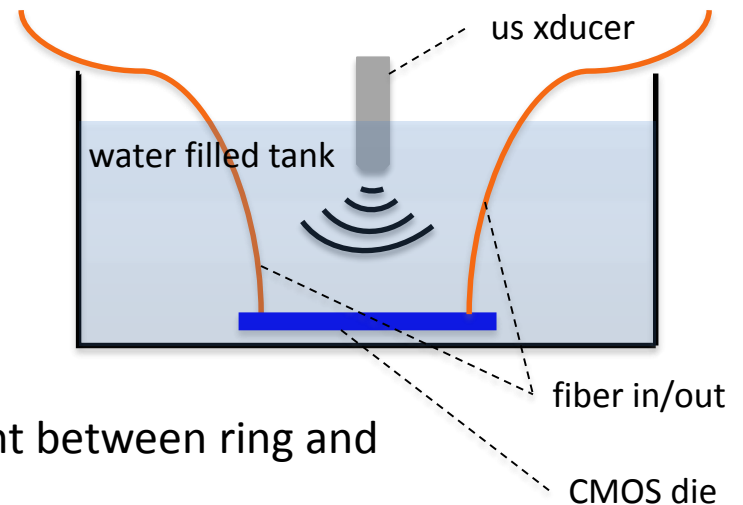
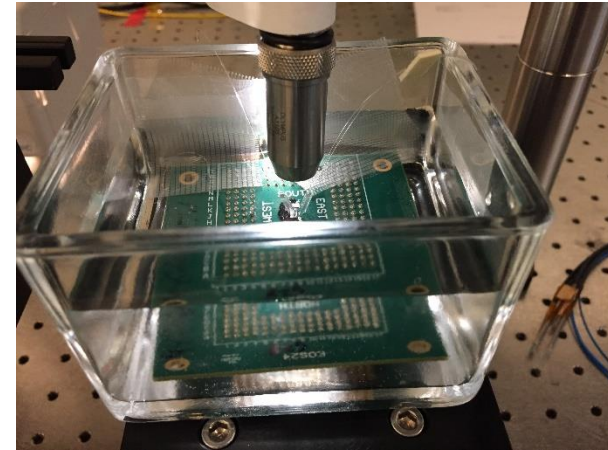
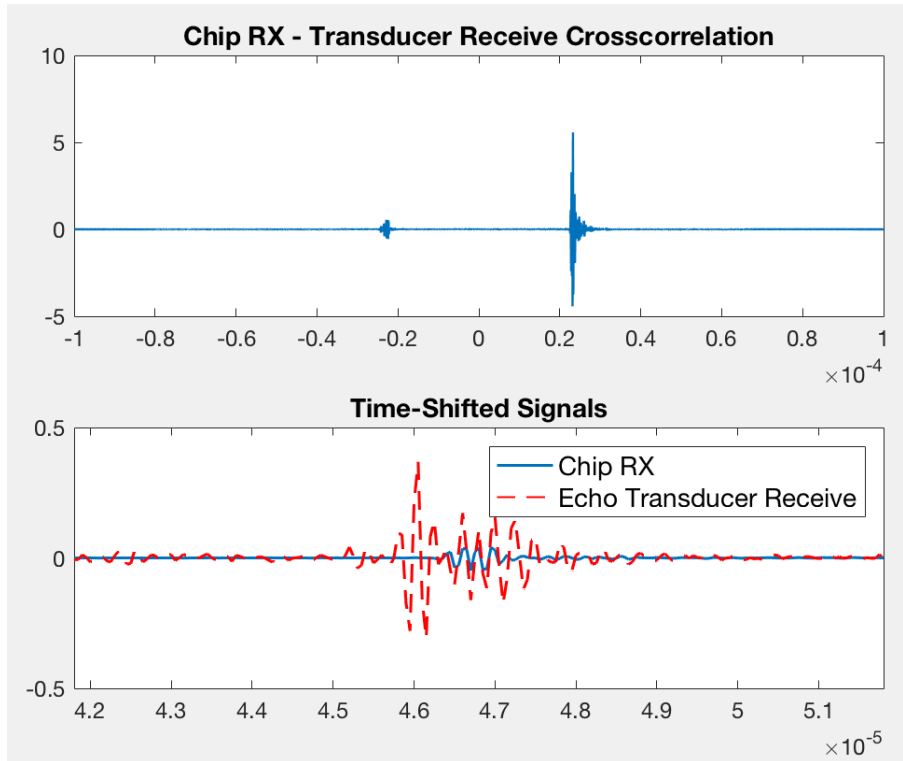


**First kinetic binding results**



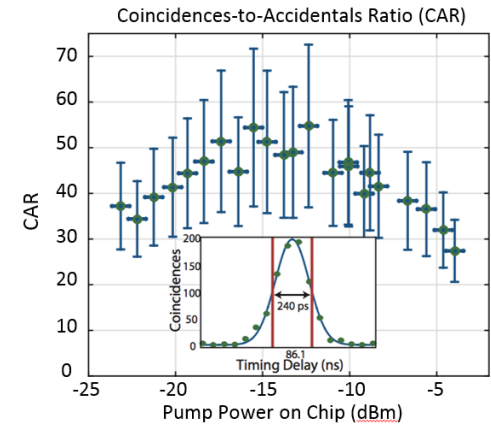
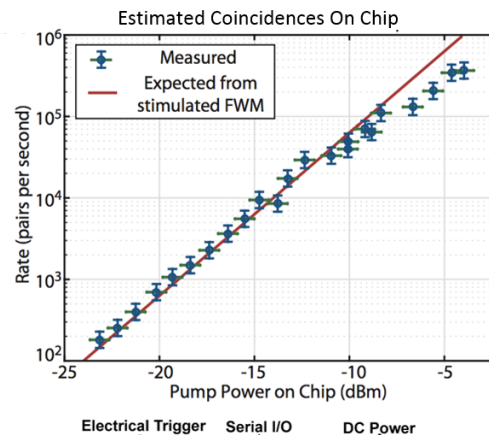
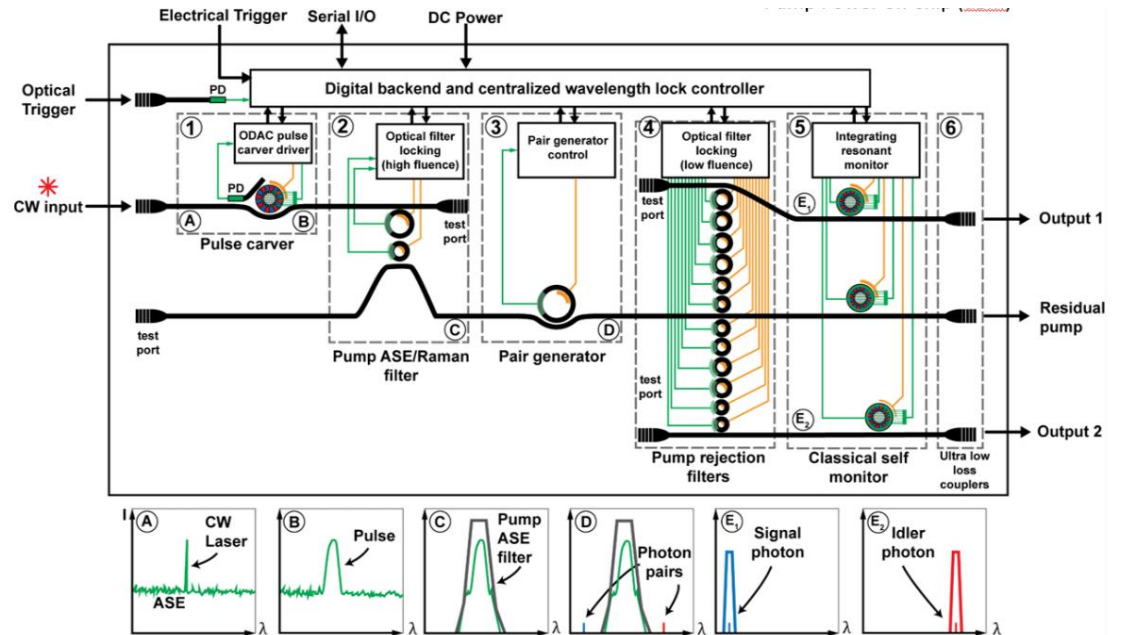
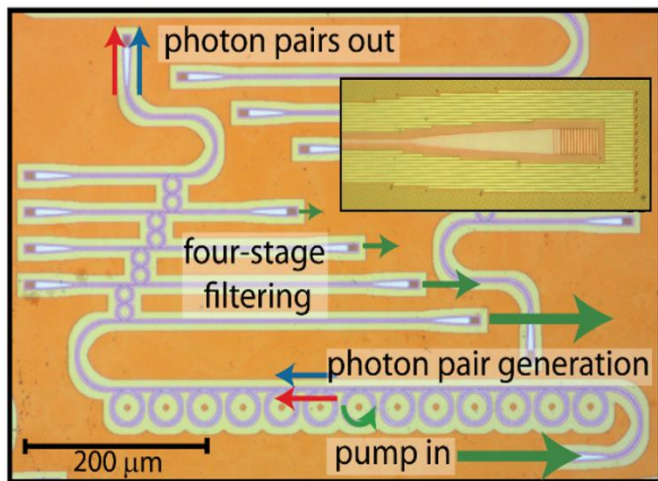
- Ultrasound RX phased array
  - Real-time 3D ultrasound imaging
- Reduced cable count and pitch compared to piezo/cmut alternatives
  - more aggressive scaling of ultrasound probes targeting IVUS, TEE
- Resonant shift induced by
  - Acoustic pressure wave straining the waveguide and causing  $\Delta n_{\text{eff}}$
  - Acoustic resonance vibration

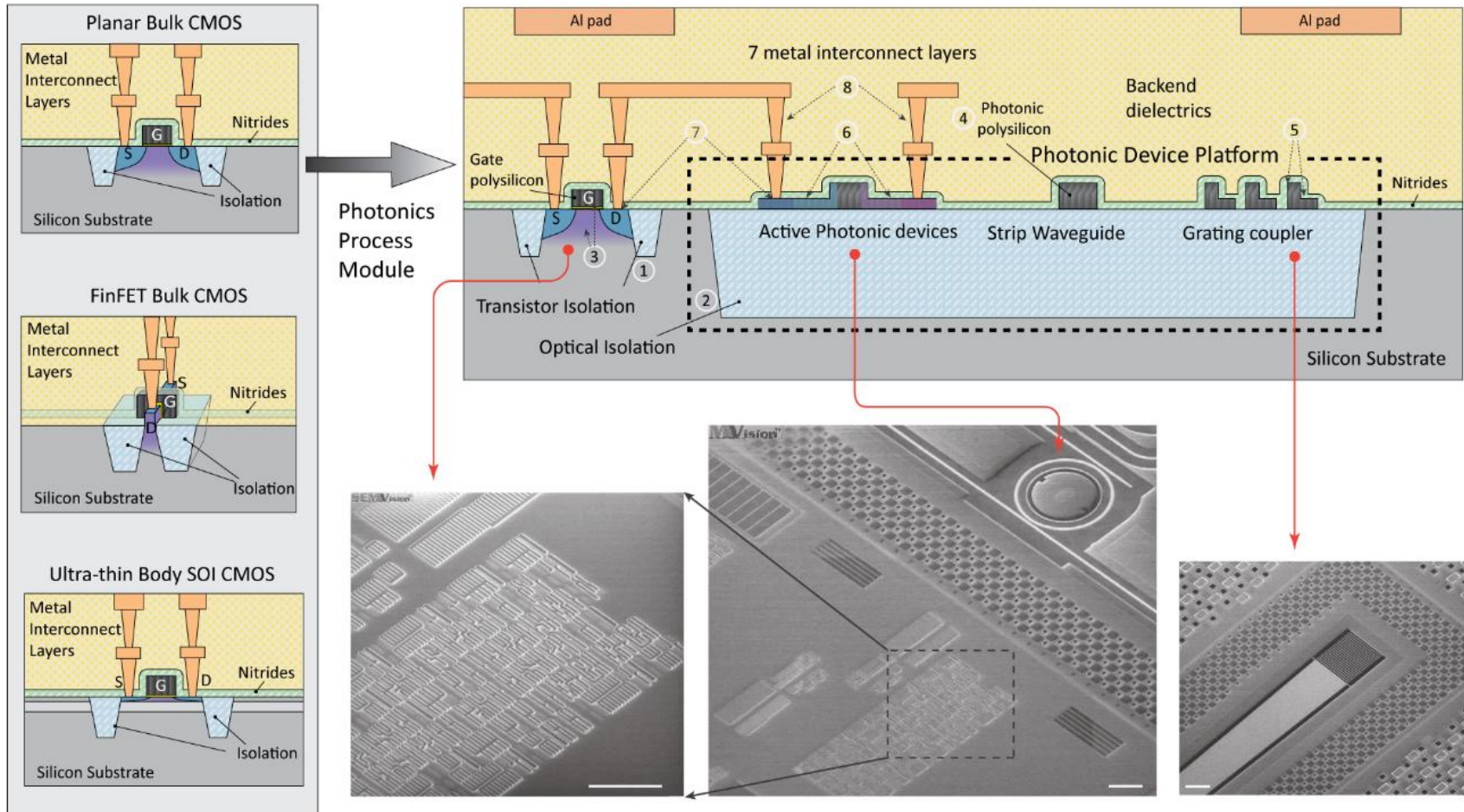




- Ring picks up the ultrasound (good agreement between ring and transducer receive response)
- Intrinsic sensitivity  $S_i = 60\text{fm/kPa}$  – comparable to existing polymer based ring related work (ring is not optimized for this application)

45nm SOI

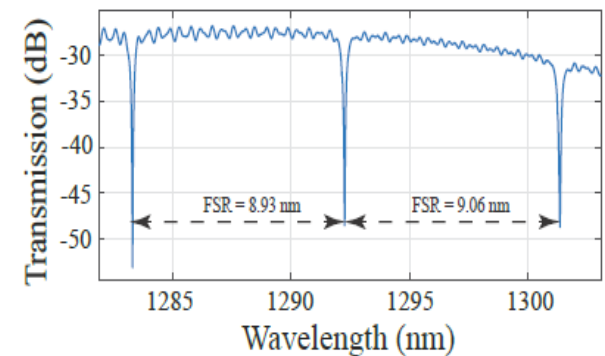
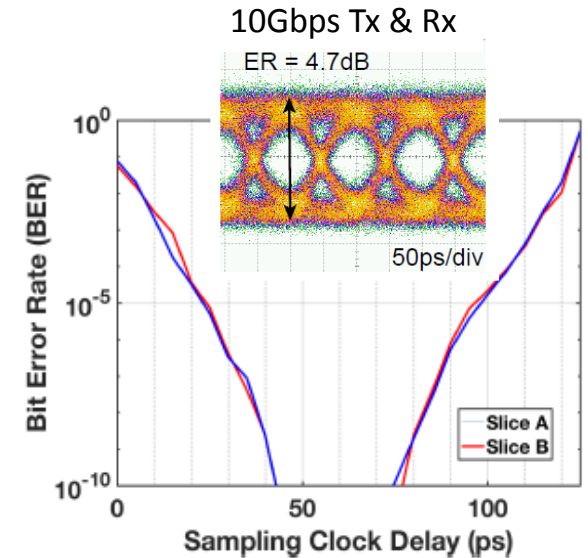
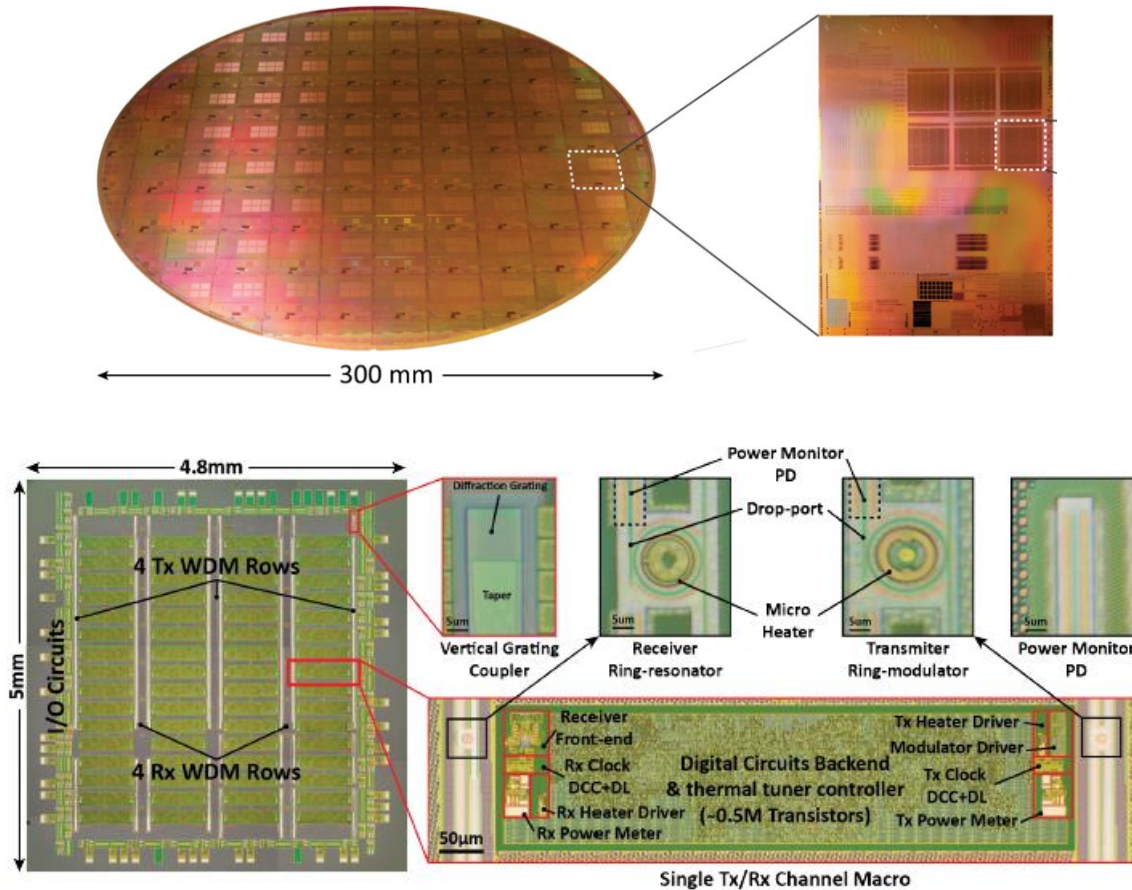




- Deposited on deep-trench oxide
- The only way to integrate photonics in advanced nodes



## First 65nm bulk CMOS wafers with working photonics and transistors!



- Silicon-photonics – enabler of new capabilities
  - Think “new on-chip inductor” or “new on-chip t-line”
- Potentially revolutionize many applications despite slowdown in CMOS scaling
- Deposited polySi-photonics key to monolithic integration with advanced transistors